

#### **Description**

The IRLML0060PBF uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



#### **General Features**

 $V_{DS} = 60V I_D = 3A$ 

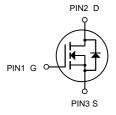
 $R_{DS(ON)}$  <  $85m\Omega$  @  $V_{GS}$ =10V

## **Application**

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
IRLML0060PBF	SOT-23	HXY MOSFET	3000PCS

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	60	V
V <sub>G</sub> S	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous	3	А
Ідм	Drain Current-Pulsed (Note 1)	10	А
P₀	Maximum Power Dissipation	1.7	W
Т,,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$ C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	73.5	°C/W



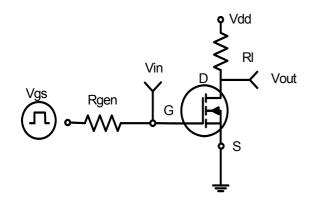
## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)	cteristics (Note 3)					
Gate Threshold Voltage	d Voltage $V_{GS(th)}$ $V_{DS}$ =V		0.8	1.3	2.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =10V, $I_D$ =3A	-	72	85	mΩ
Dialii-Source Oil-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.5A	-	85	103	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =15V,I <sub>D</sub> =2A		3	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V, F=1.0MHz	-	510	-	PF
Output Capacitance	C <sub>oss</sub>		-	34	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F-1.0WI1Z	-	26	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	6	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30V, $I_D$ =1.5A $V_{GS}$ =10V, $R_{GEN}$ =1 $\Omega$	-	15	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	$Q_g$	\/=30\/  _=3	-	7.5	-	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ =30V, $I_{D}$ =3A, $V_{GS}$ =4.5V	-	1.4	-	nC
Gate-Drain Charge	$Q_{gd}$	VGS-4.5V	-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =3A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3	Α

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

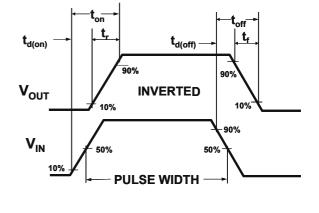
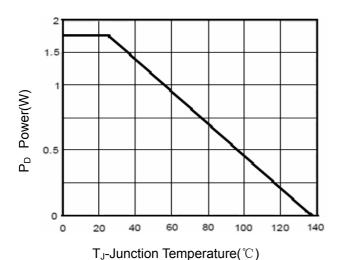


Figure 2:Switching Waveforms



**Figure 3 Power Dissipation** 

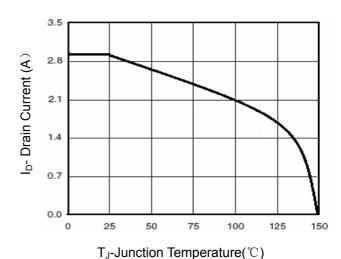
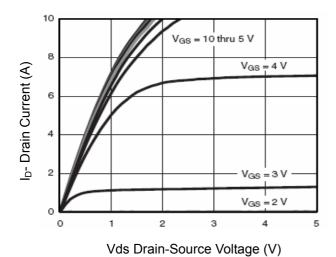


Figure 4 Drain Current



**Figure 5 Output Characteristics** 

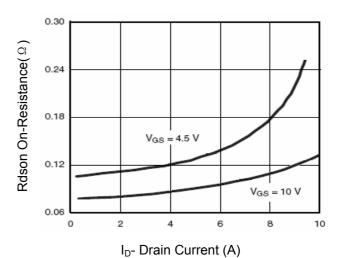
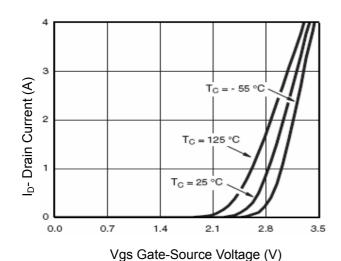
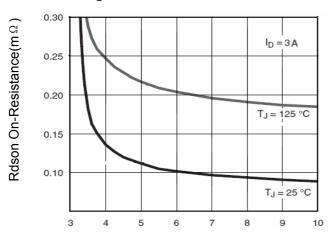


Figure 6 Drain-Source On-Resistance



**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

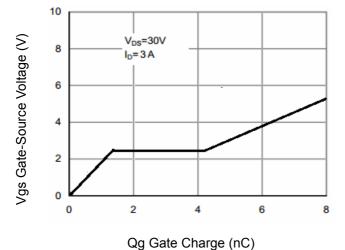


Figure 11 Gate Charge

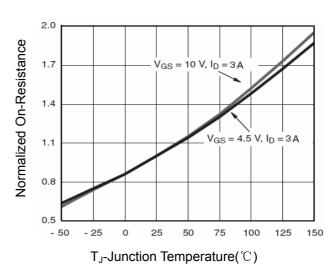
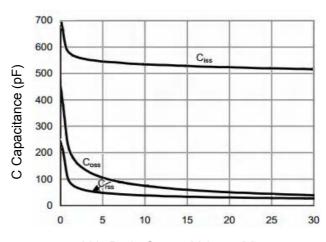
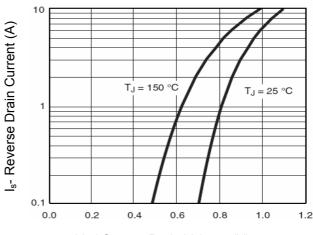


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward



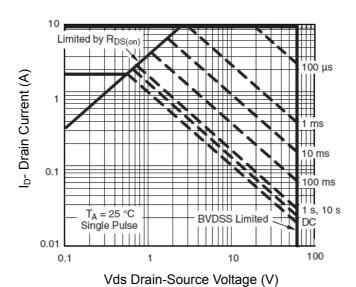
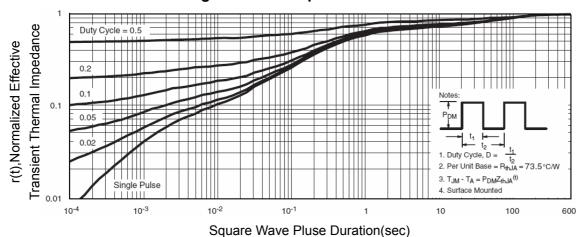


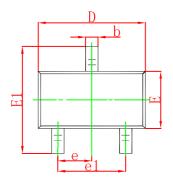
Figure 13 Safe Operation Area

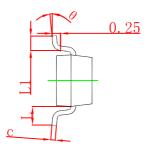


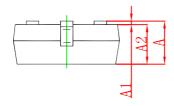
**Figure 14 Normalized Maximum Transient Thermal Impedance** 



## **SOT-23 Package Outline Dimensions**

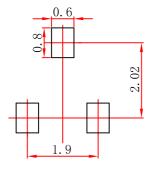






Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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